

Pb Free Plating Product

## 2SC5200



150 Watt Silicon Epitaxial Planar NPN Power Transistor

**DESCRIPTION**

- With TO-3PL package
- Complement to type 2SA1943

**APPLICATIONS**

- High current switching
- Recommended for 100W high fidelity audio frequency amplifier output stage

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

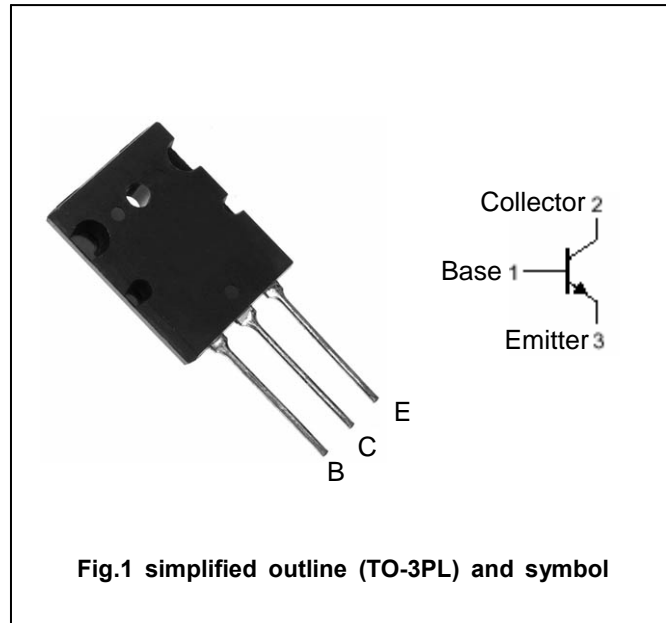


Fig.1 simplified outline (TO-3PL) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	230	V
$V_{CEO}$	Collector-emitter voltage	Open base	230	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		15	A
$I_B$	Base current		1.5	A
$P_C$	Collector power dissipation	$T_C=25$	150	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	230			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A ; I <sub>B</sub> =0.8A			3.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =7A ; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =230V ; I <sub>E</sub> =0			5	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0			5	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	55		160	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =7A ; V <sub>CE</sub> =5V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V		30		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz ; V <sub>CB</sub> =10V		200		pF

### ◆ h<sub>FE-1</sub> classifications

R	O
55-100	80-160

## Mechanical Dimensions

